

N-channel 25 V 6.1 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 31 October 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	25	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	73	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	58	W
T _j	junction temperature		-55	-	175	°C
Static char	Static characteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	6.7	7.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	5.1	6.1	mΩ
Dynamic o	Dynamic characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; V_{DS} = 12 \text{ V};$	-	2.6	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15	-	9	-	nC



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb (B
3	S	source		
4	G	gate	- q	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PSMN6R0-25YLB	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669	

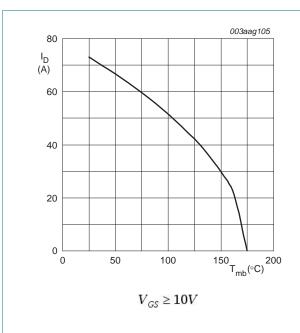
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	25	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω	-	25	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	73	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	-	52	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 4	-	292	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	58	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	220	-	V
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	53	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	292	Α
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 73 A; V_{sup} ≤ 25 V; unclamped; R_{GS} = 50 Ω; see Figure 3	-	15	mJ

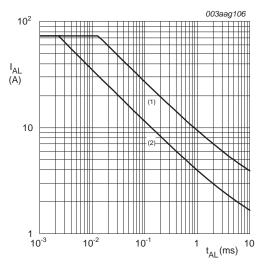
120



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$

Fig 1. Continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j \text{ (init)}} = 25^{\circ}C$; (2) $T_{j \text{ (init)}} = 100^{\circ}C$

Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

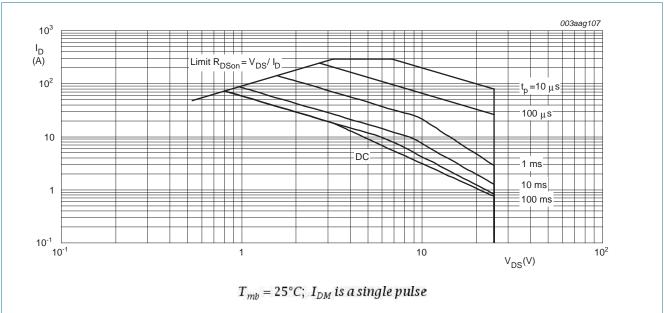
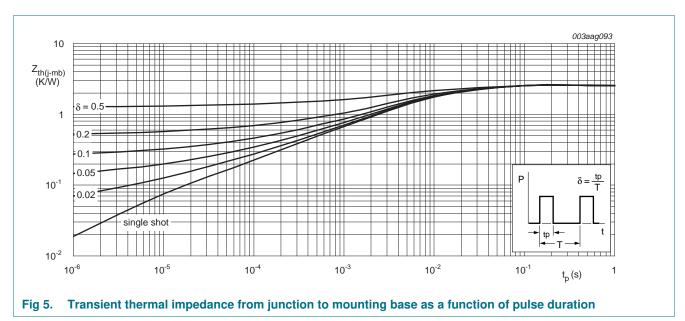


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 5	-	2.35	2.57	K/W



Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
•	racteristics			7 6		
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \mu\text{A}; V_{GS} = 0 V; T_i = 25 ^{\circ}\text{C}$	25	-	-	V
(5) 1)000	voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 V; T_i = -55 ^{\circ}\text{C}$	22.5	-	-	V
V _{GS(th)}	gate-source threshold voltage	<u> </u>	1.05	1.42	1.95	V
		I _D = 10 mA; V _{DS} = V _{GS} ; T _i = 150 °C	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	6.7	7.9	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 150 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	13	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	5.1	6.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 150 °C;$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	10.1	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz	-	1.62	3.24	Ω
Dynamic (characteristics					
Q _{G(tot)} total gate charge	total gate charge	$I_D = 20 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	19.3	-	nC
		$I_D = 20 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see Figure 14; see Figure 15	-	9	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	17.7	-	nC
Q_{GS}	gate-source charge	$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	2.6	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	1.9	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.7	-	nC
Q_{GD}	gate-drain charge		-	2.6	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 20 \text{ A}$; $V_{DS} = 12 \text{ V}$; see Figure 14; see Figure 15	-	2.44	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1099	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	337	-	pF
C _{rss}	reverse transfer capacitance		-	99	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 12 V; R_L = 0.6 Ω ; V_{GS} = 4.5 V;	-	16	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	17	-	ns
t _{d(off)}	turn-off delay time		-	30	-	ns
				9		

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q_{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; f = 1 \text{ MHz}$	-	6.6	-	nC
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 20 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.85	1.1	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	27	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}$	-	18	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 20 \text{ A};$	-	15	-	ns
t _b	reverse recovery fall time	$dl_S/dt = -100 A/\mu s; V_{DS} = 12 V;$ see Figure 18	-	12	-	ns

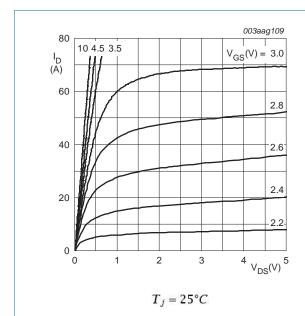


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

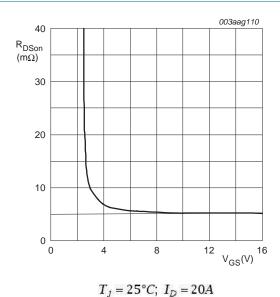


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

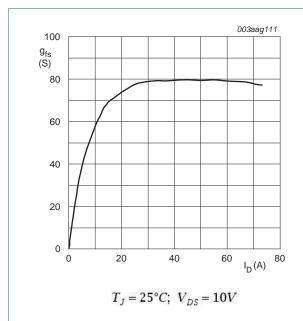


Fig 8. Forward transconductance as a function of drain current; typical values

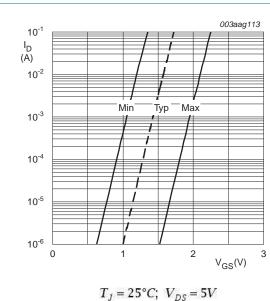


Fig 10. Sub-threshold drain current as a function of gate-source voltage

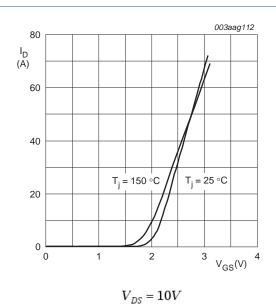


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

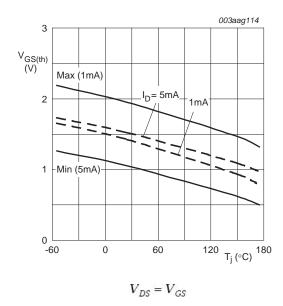


Fig 11. Gate-source threshold voltage as a function of junction temperature

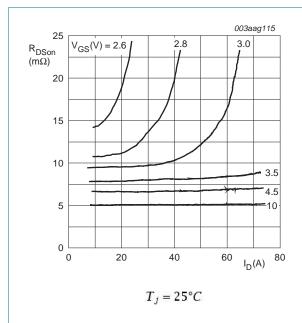


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

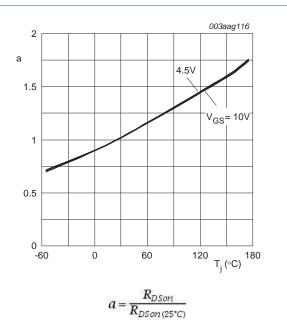


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

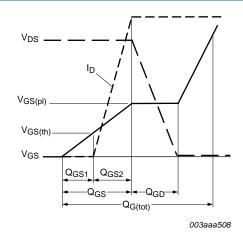
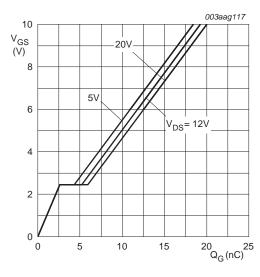


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; I_D = 20A$

Fig 15. Gate-source voltage as a function of gate charge; typical values

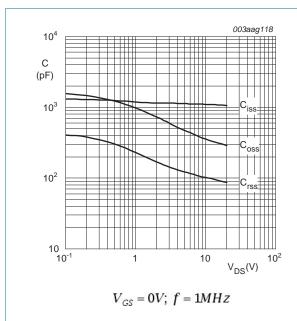


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

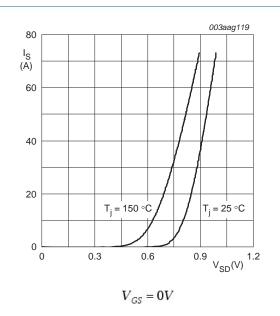


Fig 17. Source current as a function of source-drain voltage; typical values

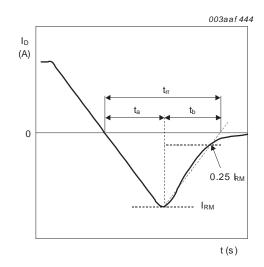


Fig 18. Reverse recovery timing definition

7. Package outline



SOT669

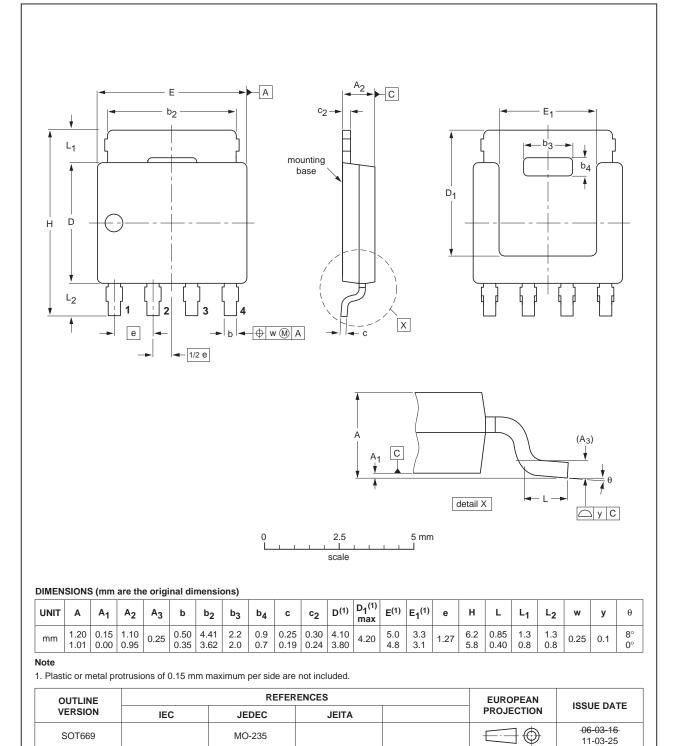


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

N-channel 25 V 6.1 mΩ logic level MOSFET in LFPAK using NextPower technology

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R0-25YLB v.2	20111031	Product data sheet	-	PSMN6R0-25YLB v.1
Modifications:	Status changed froVarious changes to	m preliminary to product. content.		
PSMN6R0-25YLB v.1	20110908	Preliminary data sheet	-	-

N-channel 25 V 6.1 mΩ logic level MOSFET in LFPAK using NextPower technology

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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